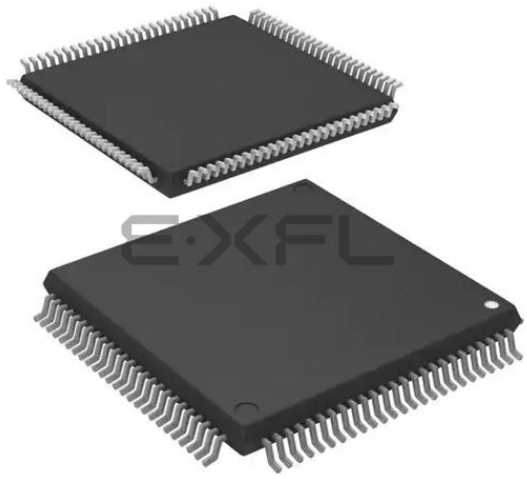
Renesas Electronics America Inc - M30302GGPGP#U3 Datasheet



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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	M16C/30
Core Size	16-Bit
Speed	16MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	87
Program Memory Size	96KB (96K x 8)
Program Memory Type	One Time Flash
EEPROM Size	-
RAM Size	5K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 3.6V
Data Converters	A/D 18x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30302ggpgp-u3

Table 1.3 Product List (2) **As of March 2007**

Part No.	ROM Capacity	RAM Capacity	package code (1)	Remarks
M30302FAPFP	96 K + 4 Kbytes	5 Kbytes	PRQP0100JB-A	Flash memory version(2)
M30302FAPGP			PLQP0100KB-A	
M30302FCPFP	128 K + 4 Kbytes		PRQP0100JB-A	
M30302FCPGP			PLQP0100KB-A	
M30302FEPFP	192 K + 4 Kbytes	6 Kbytes	PRQP0100JB-A	
M30302FEPGP			PLQP0100KB-A	
M30302SPFP	-	6 Kbytes	PRQP0100JB-A	ROM-less version
M30302SPGP			PLQP0100KB-A	

(D): Under development
(P): Under planning
NOTES:
1. Previous package codes are as follows.
   PRQP0100JB-A : 100P6S-A,
   PLQP0100KB-A : 100P6Q-A
2. Block A (4-Kbytes space) is available in flash memory version.

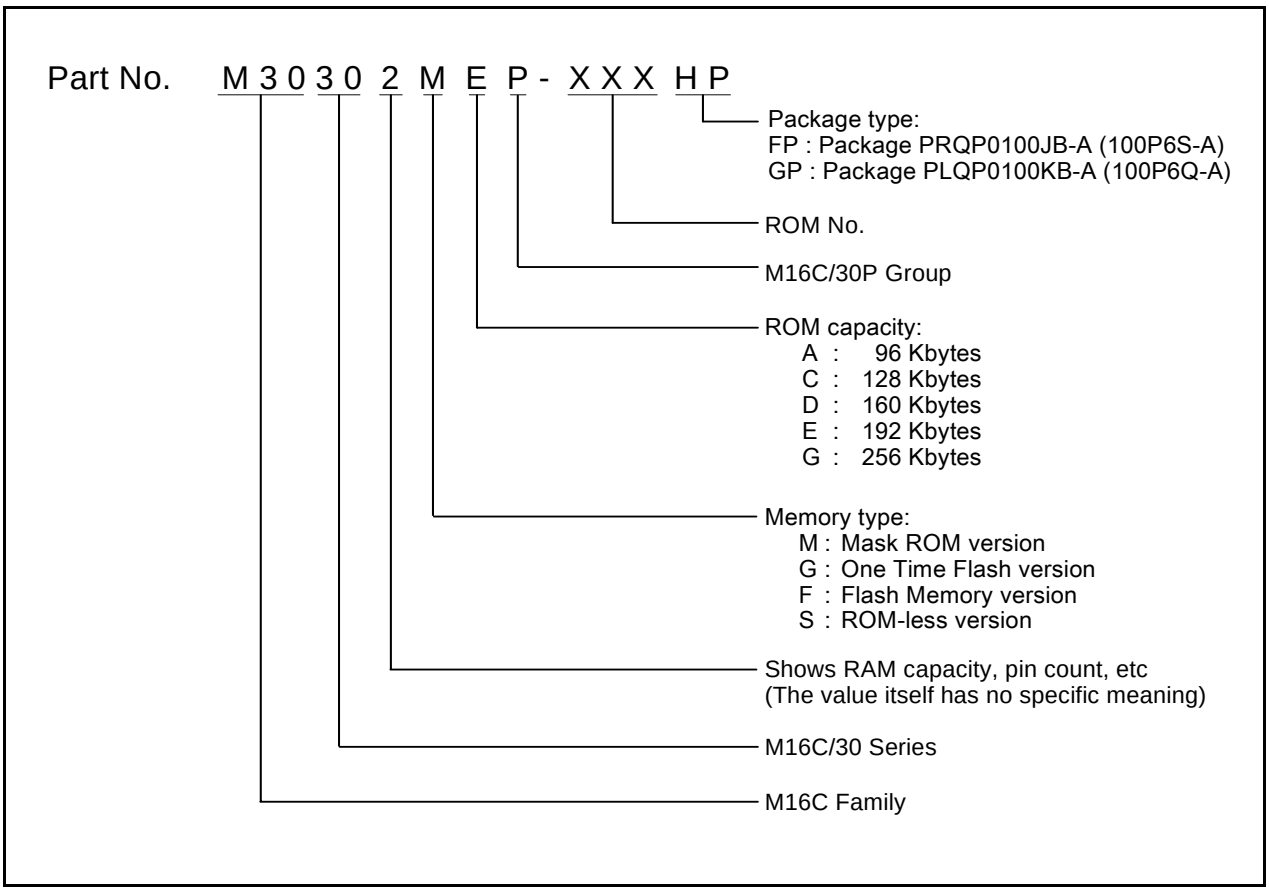


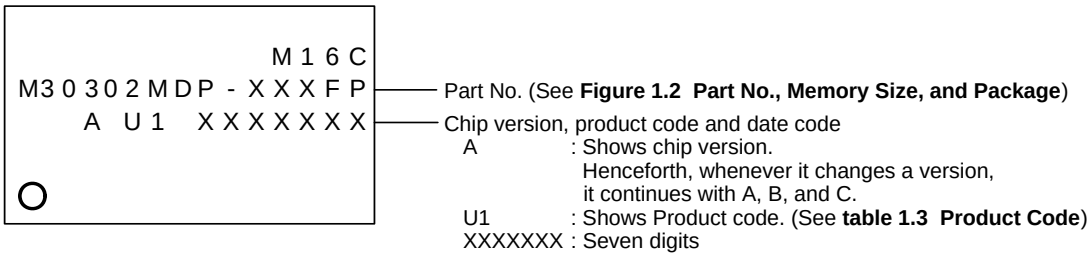
Figure 1.2 Part No., Memory Size, and Package

Table 1.4 Product Code of MASK ROM version for M16C/30P

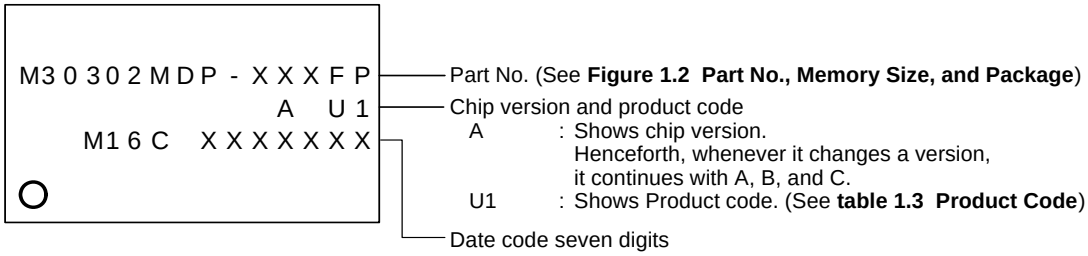
Product Code	Package	Operating Ambient Temperature
U1	Lead-free	-20°C to 85°C
U4		-40°C to 85°C

PRQP0100JB-A (100P6S-A)

1. Standard Renesas Mark

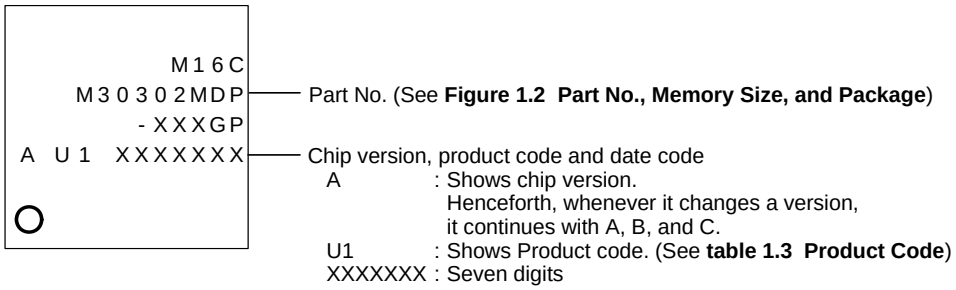


2. Customer's Parts Number + Renesas catalog name

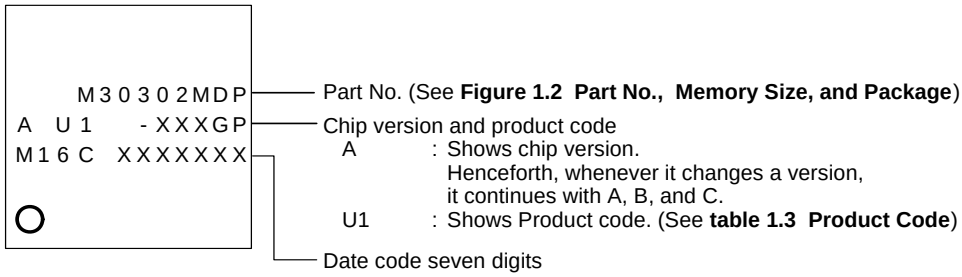


PLQP0100KB-A (100P6Q-A)

1. Standard Renesas Mark



2. Customer's Parts Number + Renesas catalog name



NOTES:
1. Refer to the **mark specification form** for details of the Mask ROM version marking.

Figure 1.3 Marking Diagram of Mask ROM Version for M16C/30P (Top View)

Table 1.5 Product Code of One Time Flash version, Flash Memory version, and ROM-less version for M16C/30P

	Product Code	Package	Internal ROM		Operating Ambient Temperature
			Program and Erase Endurance	Temperature Range	
One Time Flash version	U3	Lead-free	0	0°C to 60°C	-40°C to 85°C
	U5				-20°C to 85°C
Flash Memory version	U3	Lead-free	100	0°C to 60°C	-40°C to 85°C
	U5				-20°C to 85°C
ROM-less version	U3	Lead-free	–	–	-40°C to 85°C
	U5				-20°C to 85°C

NOTES:The one time flash version can be written once only.

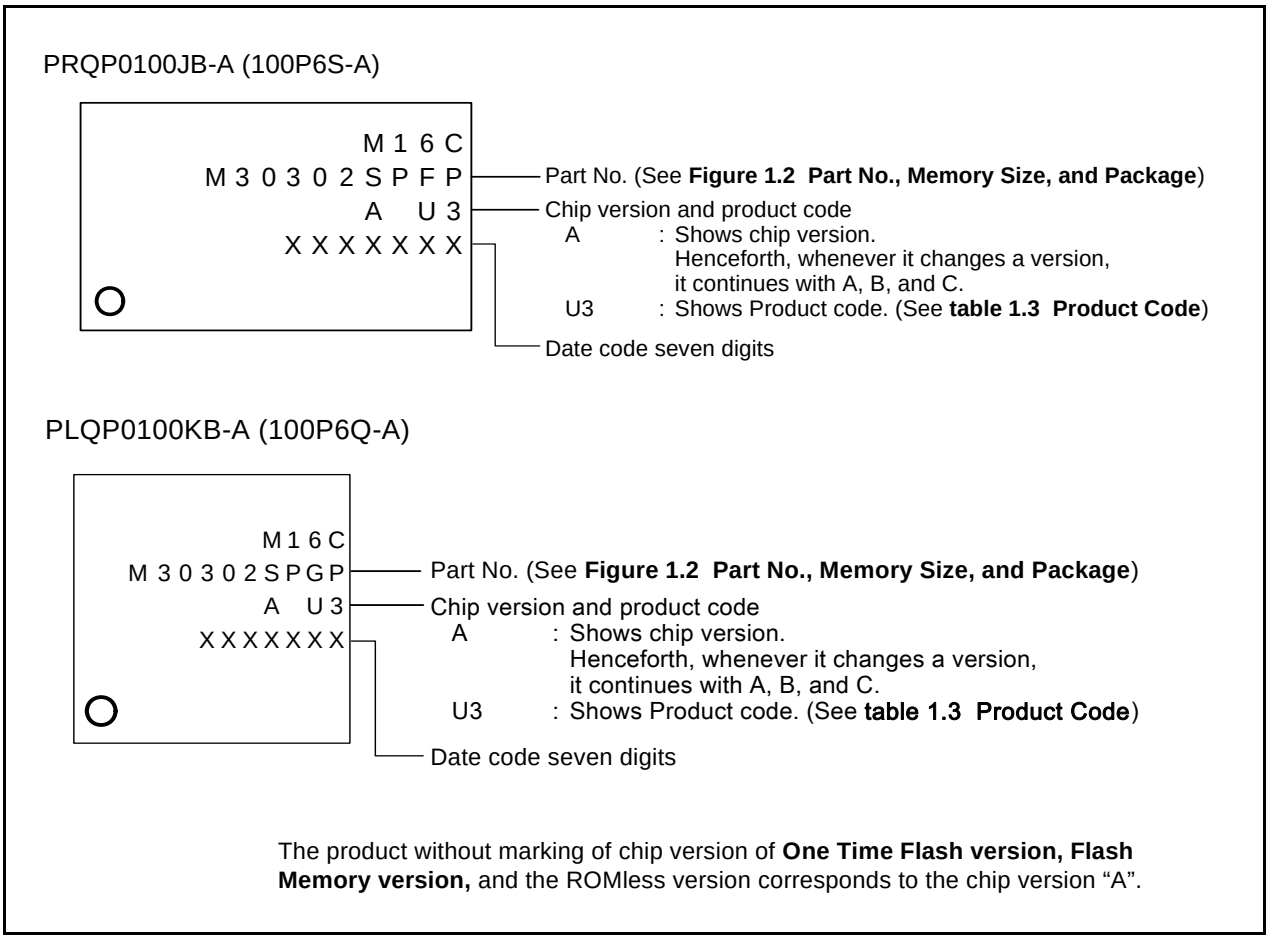


Figure 1.4 Marking Diagram of One Time Flash version, Flash Memory version, and ROM-less Version for M16C/30P (Top View)

1.5 Pin Configuration

Figures 1.5 to 1.6 show the pin configurations (top view).

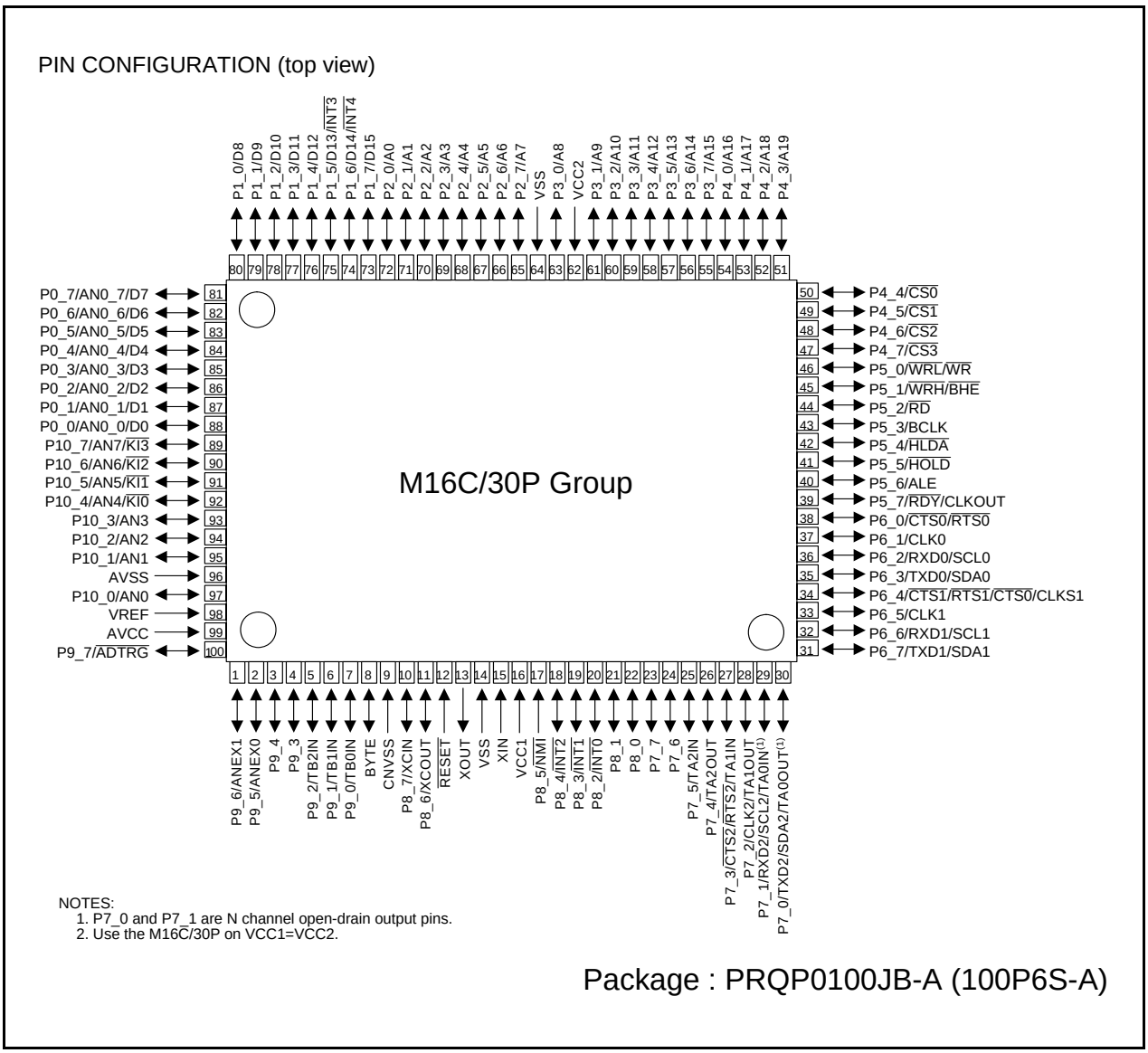


Figure 1.5 Pin Configuration (Top View)

4. Special Function Register (SFR)

SFR(Special Function Register) is the control register of peripheral functions. Tables 4.1 to 4.5 list the SFR information.

Table 4.1 SFR Information (1) (1)

Address	Register	Symbol	After Reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0 (2)	PM0	00000000b(CNVSS pin is "L") 00000011b(CNVSS pin is "H")
0005h	Processor Mode Register 1	PM1	00XXX0X0b
0006h	System Clock Control Register 0	CM0	01001000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h	Chip Select Control Register	CSR	00000001b
0009h	Address Match Interrupt Enable Register	AIER	XXXXXX00b
000Ah	Protect Register	PRCR	XX000000b
000Bh			
000Ch			
000Dh			
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDC	00XXXXXXb
0010h 0011h 0012h	Address Match Interrupt Register 0	RMAD0	00h 00h X0h
0013h			
0014h 0015h 0016h	Address Match Interrupt Register 1	RMAD1	00h 00h X0h
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch			
001Dh			
001Eh			
001Fh			
0020h 0021h 0022h	DMA0 Source Pointer	SAR0	XXh XXh XXh
0023h			
0024h 0025h 0026h	DMA0 Destination Pointer	DAR0	XXh XXh XXh
0027h			
0028h 0029h	DMA0 Transfer Counter	TCR0	XXh XXh
002Ah			
002Bh			
002Ch	DMA0 Control Register	DM0CON	00000X00b
002Dh			
002Eh			
002Fh			
0030h 0031h 0032h	DMA1 Source Pointer	SAR1	XXh XXh XXh
0033h			
0034h 0035h 0036h	DMA1 Destination Pointer	DAR1	XXh XXh XXh
0037h			
0038h 0039h	DMA1 Transfer Counter	TCR1	XXh XXh
003Ah			
003Bh			
003Ch	DMA1 Control Register	DM1CON	00000X00b
003Dh			
003Eh			
003Fh			

NOTES:
1. The blank areas are reserved and cannot be accessed by users.
2. The PM00 and PM01 bits do not change at software reset.

X : Nothing is mapped to this bit

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter		Condition	Rated Value	Unit
V_{CC}	Supply Voltage(V_{CC1}=V_{CC2})		V_{CC1}=V_{CC2}=AVcc	–0.3 to 6.5	V
AVcc	Analog Supply Voltage		V_{CC1}=V_{CC2}=AVcc	–0.3 to 6.5	V
V_I	Input Voltage	$\overline{\text{RESET}}$, CNVSS, BYTE, P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, VREF, XIN		–0.3 to V_{CC}+0.3	V
		P7_0, P7_1		–0.3 to 6.5	V
V_O	Output Voltage	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, XOUT		–0.3 to V_{CC}+0.3	V
		P7_0, P7_1		–0.3 to 6.5	V
P_d	Power Dissipation		–40°C<T_{opr}≤85°C	300	mW
T_{opr}	Operating Ambient Temperature	When the Microcomputer is Operating		–20 to 85 / –40 to 85	°C
		One Time Flash Program Erase		0 to 60	
		Flash Program Erase		0 to 60	
T_{stg}	Storage Temperature			–65 to 150	°C

Table 5.2 Recommended Operating Conditions (1)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
V_{CC}	Supply Voltage (V_{CC1}=V_{CC2})		2.7	5.0	5.5	V
AVcc	Analog Supply Voltage			Vcc		V
Vss	Supply Voltage			0		V
AVss	Analog Supply Voltage			0		V
V_{IH}	HIGH Input Voltage	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7	0.8Vcc		Vcc	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (during single-chip mode)	0.8Vcc		Vcc	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (data input during memory expansion and microprocessor mode)	0.5Vcc		Vcc	V
		P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, XIN, $\overline{\text{RESET}}$, CNVSS, BYTE	0.8Vcc		Vcc	V
		P7_0, P7_1	0.8Vcc		6.5	V
V_{IL}	LOW Input Voltage	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7	0		0.2Vcc	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (during single-chip mode)	0		0.2Vcc	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (data input during memory expansion and microprocessor mode)	0		0.16Vcc	V
		P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, XIN, $\overline{\text{RESET}}$, CNVSS, BYTE	0		0.2Vcc	V
$I_{OH(peak)}$	HIGH Peak Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7			−10.0	mA
$I_{OH(avg)}$	HIGH Average Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7			−5.0	mA
$I_{OL(peak)}$	LOW Peak Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7			10.0	mA
$I_{OL(avg)}$	LOW Average Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7			5.0	mA
f(XIN)	Main Clock Input Oscillation Frequency (4)	Vcc=3.0V to 5.5V	0		16	MHz
		Vcc=2.7V to 3.0V	0		20×V_{CC1}−44	MHz
f(XCIN)	Sub-Clock Oscillation Frequency			32.768	50	kHz
f(BCLK)	CPU Operation Clock		0		16	MHz

NOTES:
1. Referenced to V_{CC1} = V_{CC2} = 2.7 to 5.5V at T_{opr} = −20 to 85°C / −40 to 85°C unless otherwise specified.
2. The Average Output Current is the mean value within 100ms.
3. The total $I_{OL(peak)}$ for ports P0, P1, P2, P8_6, P8_7, P9 and P10 must be 80mA max. The total $I_{OL(peak)}$ for ports P3, P4, P5, P6, P7 and P8_0 to P8_4 must be 80mA max. The total $I_{OH(peak)}$ for ports P0, P1, and P2 must be −40mA max. The total $I_{OH(peak)}$ for ports P3, P4 and P5 must be −40mA max. The total $I_{OH(peak)}$ for ports P6, P7, and P8_0 to P8_4 must be −40mA max.
   The total $I_{OH(peak)}$ for ports P8_6, P8_7 and P9 must be −40mA max. Set Average Output Current to 1/2 of peak.
4. Relationship between main clock oscillation frequency, and supply voltage.

Main clock input oscillation frequency

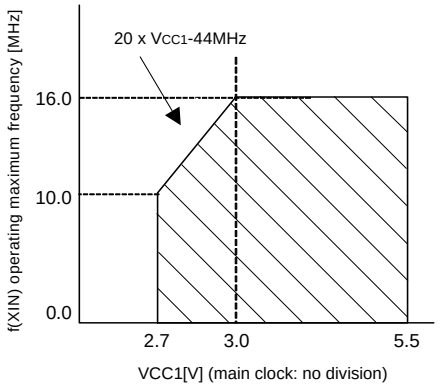


Table 5.4 Flash Memory Version Electrical Characteristics (1)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (2)		100(3)			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (4)		10			year

NOTES:
1. Referenced to V_{CC1}=4.5 to 5.5V, 3.0 to 3.6V at Topr = 0 to 60 °C (U3, U5) unless otherwise specified.
2. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is 100, each block can be erased 100 times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
3. Maximum number of E/W cycles for which operation is guaranteed.
4. Topr = -40 to 85 °C (U3) / -20 to 85 °C (U5).

Table 5.5 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 3.3 ± 0.3 V or 5.0 ± 0.5 (T_{opr} = 0°C to 60°C)	V_{CC1}=2.7 to 5.5 V (T_{opr} = -40°C to 85°C (U3) -20°C to 85°C (U5))

Table 5.8 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for Internal Power Supply Stabilization During Powering-On	V_{CC}=2.7V to 5.5V			2	ms
$t_{d(R-S)}$	STOP Release Time				1500	µs
$t_{d(W-S)}$	Low Power Dissipation Mode Wait Mode Release Time				1500	µs

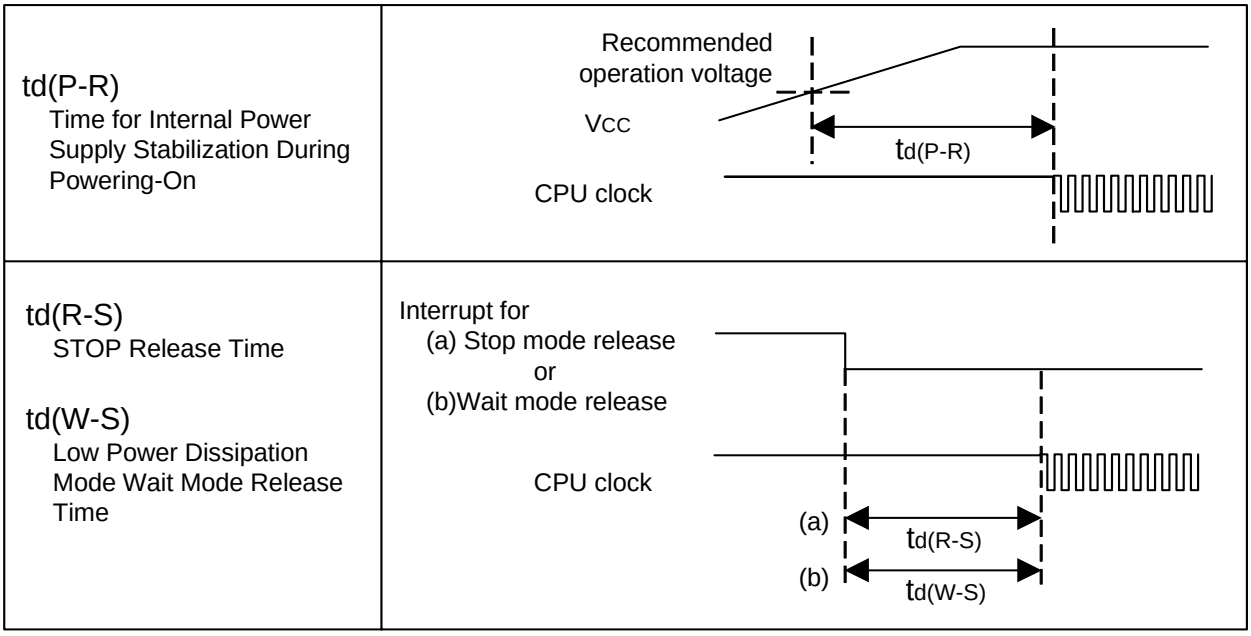


Figure 5.1 Power Supply Circuit Timing Diagram

Table 5.10 Electrical Characteristics (2) (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
I_{CC}	Power Supply Current (V_{CC1}=V_{CC2}=4.0V to 5.5V)	In single-chip mode, the output pins are open and other pins are V_{SS}	Mask ROM	f(XIN)=16MHz No division		10	15	mA
			One Time Flash	f(XIN)=16MHz, No division		10	18	mA
			Flash Memory	f(XIN)=16MHz, No division		12	18	mA
			One Time Flash	f(XIN)=10MHz, VCC1=5.0V		15		mA
			Flash Memory Program	f(XIN)=10MHz, VCC1=5.0V		15		mA
			Flash Memory Erase	f(XIN)=10MHz, VCC1=5.0V		25		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM (3)		25		µA
			One Time Flash	f(XCIN)=32kHz Low power dissipation mode, RAM (3)		25		µA
				f(XCIN)=32kHz Low power dissipation mode, Flash Memory (3)		350		µA
			Flash Memory	f(XCIN)=32kHz Low power dissipation mode, RAM (3)		25		µA
				f(XCIN)=32kHz Low power dissipation mode, Flash Memory (3)		420		µA
			Mask ROM One Time Flash Flash Memory	f(XCIN)=32kHz Wait mode (2), Oscillation capability High		7.5		µA
				f(XCIN)=32kHz Wait mode (2), Oscillation capability Low		2.0		µA
				Stop mode Topr =25°C		0.8	3.0	µA

NOTES:
1. Referenced to V_{CC1}=V_{CC2}=4.2 to 5.5V, V_{SS} = 0V at T_{opr} = –20 to 85°C / –40 to 85°C, f(XIN)=16MHz unless otherwise specified.
2. With one timer operated using fC32.
3. This indicates the memory in which the program to be executed exists.

$V_{CC1}=V_{CC2}=5V$

Timing Requirements

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.13 Timer A Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	100		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	40		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	40		ns

Table 5.14 Timer A Input (Gating Input in Timer Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	400		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	200		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	200		ns

Table 5.15 Timer A Input (External Trigger Input in One-shot Timer Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	200		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	100		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	100		ns

Table 5.16 Timer A Input (External Trigger Input in Pulse Width Modulation Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	100		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	100		ns

Table 5.17 Timer A Input (Counter Increment/Decrement Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(UP)}$	TAiOUT Input Cycle Time	2000		ns
$t_{w(UPH)}$	TAiOUT Input HIGH Pulse Width	1000		ns
$t_{w(UPL)}$	TAiOUT Input LOW Pulse Width	1000		ns
$t_{su(UP-TIN)}$	TAiOUT Input Setup Time	400		ns
$t_{h(TIN-UP)}$	TAiOUT Input Hold Time	400		ns

Table 5.18 Timer A Input (Two-phase Pulse Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	800		ns
$t_{su(TAIN-TAOUT)}$	TAiOUT Input Setup Time	200		ns
$t_{su(TAOUT-TAIN)}$	TAiIN Input Setup Time	200		ns

$V_{CC1}=V_{CC2}=5V$

Timing Requirements

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.19 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on one edge)	100		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on one edge)	40		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on one edge)	40		ns
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on both edges)	200		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on both edges)	80		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on both edges)	80		ns

Table 5.20 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	400		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	200		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	200		ns

Table 5.21 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	400		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	200		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	200		ns

Table 5.22 A/D Trigger Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(AD)}$	$\overline{\text{ADTRG}}$ Input Cycle Time	1000		ns
$t_{w(ADL)}$	$\overline{\text{ADTRG}}$ input LOW Pulse Width	125		ns

Table 5.23 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi Input Cycle Time	200		ns
$t_{w(CKH)}$	CLKi Input HIGH Pulse Width	100		ns
$t_{w(CKL)}$	CLKi Input LOW Pulse Width	100		ns
$t_{d(C-Q)}$	TXDi Output Delay Time		80	ns
$t_{h(C-Q)}$	TXDi Hold Time	0		ns
$t_{su(D-C)}$	RXDi Input Setup Time	70		ns
$t_{h(C-D)}$	RXDi Input Hold Time	90		ns

Table 5.24 External Interrupt $\overline{\text{INTi}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{\text{INTi}}$ Input HIGH Pulse Width	250		ns
$t_{w(INL)}$	$\overline{\text{INTi}}$ Input LOW Pulse Width	250		ns

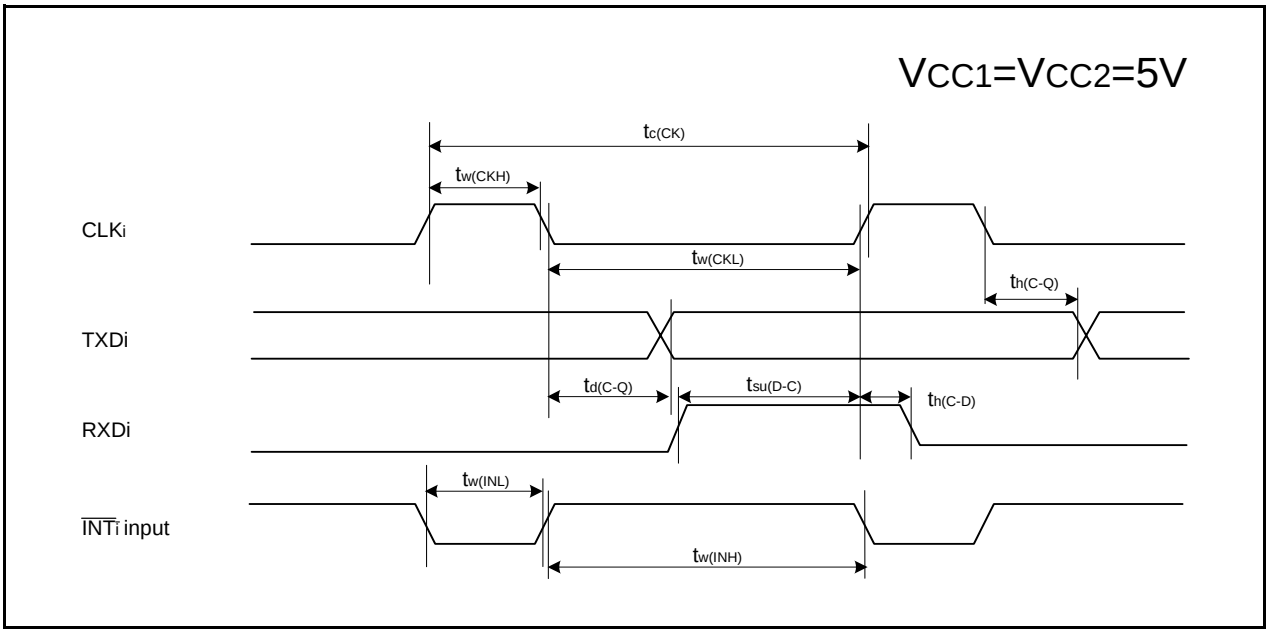
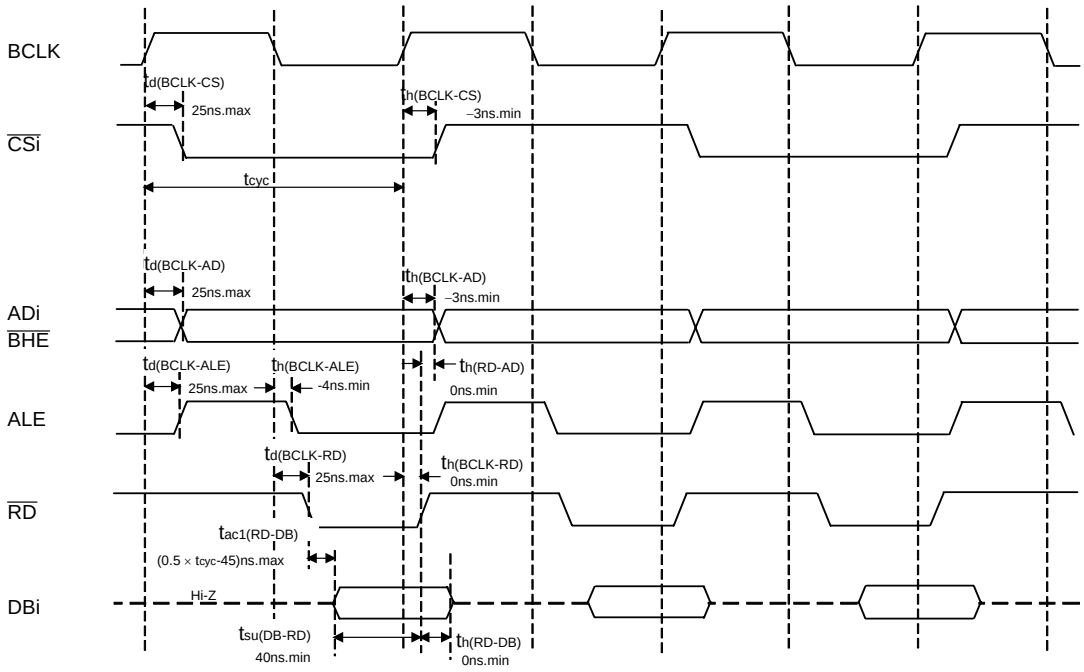


Figure 5.4 Timing Diagram (2)

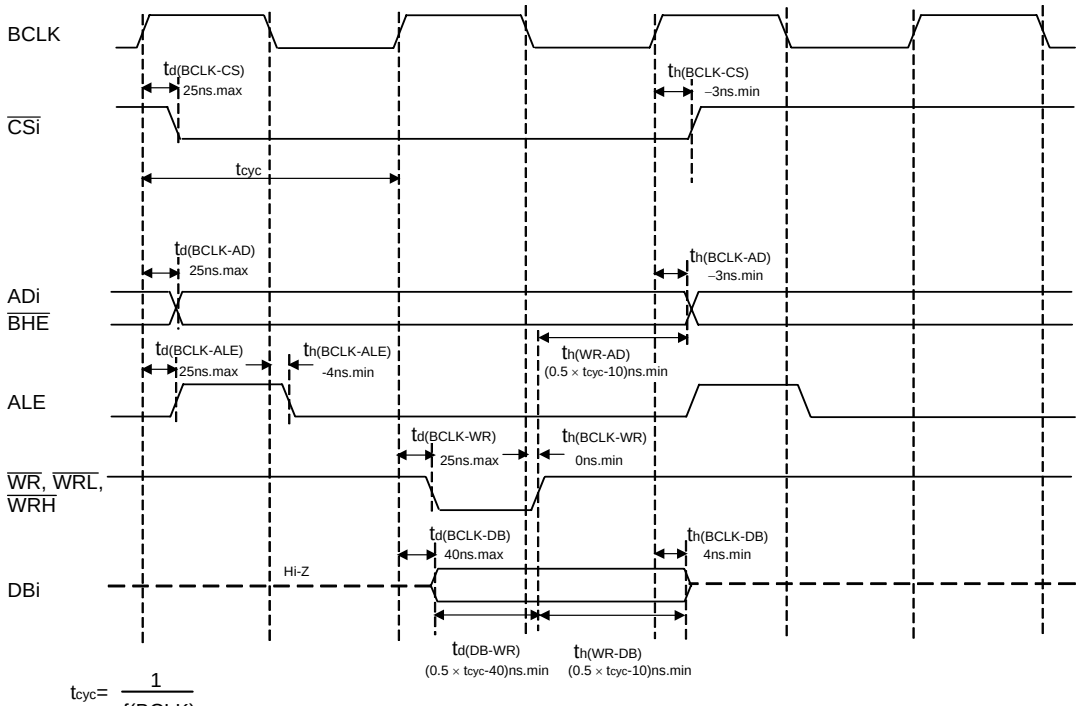
Memory Expansion Mode, Microprocessor Mode
(For setting with no wait**)**

$V_{CC1}=V_{CC2}=5V$

Read timing



Write timing



$$t_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
· $V_{CC1}=V_{CC2}=5V$
· Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
· Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

Figure 5.6 Timing Diagram (4)

$V_{CC1}=V_{CC2}=3V$

Timing Requirements

(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.29 External Clock Input (XIN input)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External Clock Input Cycle Time	(NOTE 2)		ns
$t_{w(H)}$	External Clock Input HIGH Pulse Width	(NOTE 3)		ns
$t_{w(L)}$	External Clock Input LOW Pulse Width	(NOTE 3)		ns
t_r	External Clock Rise Time		(NOTE 4)	ns
t_f	External Clock Fall Time		(NOTE 4)	ns

NOTES:

1. The condition is V_{CC1}=V_{CC2}=2.7 to 3.0V.
2. Calculated according to the V_{CC1} voltage as follows:

$$\frac{10^{-6}}{20 \times V_{CC1} - 44} \text{ [ns]}$$

3. Calculated according to the V_{CC1} voltage as follows:

$$\frac{10^{-6}}{20 \times V_{CC1} - 44} \times 0.4 \text{ [ns]}$$

4. Calculated according to the V_{CC1} voltage as follows:

$$-10 \times V_{CC1} + 45 \text{ [ns]}$$

Table 5.30 Memory Expansion Mode and Microprocessor Mode

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{ac1(RD-DB)}$	Data Input Access Time (for setting with no wait)		(NOTE 1)	ns
$t_{ac2(RD-DB)}$	Data Input Access Time (for setting with wait)		(NOTE 2)	ns
$t_{su(DB-RD)}$	Data Input Setup Time	50		ns
$t_{su(RDY-BCLK)}$	$\overline{RDY}$ Input Setup Time	40		ns
$t_{su(HOLD-BCLK)}$	$\overline{HOLD}$ Input Setup Time	50		ns
$t_{h(RD-DB)}$	Data Input Hold Time	0		ns
$t_{h(BCLK-RDY)}$	$\overline{RDY}$ Input Hold Time	0		ns
$t_{h(BCLK-HOLD)}$	$\overline{HOLD}$ Input Hold Time	0		ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 60 \text{ [ns]}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n - 0.5) \times 10^9}{f(BCLK)} - 60 \text{ [ns]}$$ n is "2" for 1-wait setting.

$V_{CC1}=V_{CC2}=3V$

Timing Requirements

(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.37 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on one edge)	150		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on one edge)	60		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on one edge)	60		ns
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on both edges)	300		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on both edges)	120		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on both edges)	120		ns

Table 5.38 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	600		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	300		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	300		ns

Table 5.39 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	600		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	300		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	300		ns

Table 5.40 A/D Trigger Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(AD)}$	$\overline{\text{ADTRG}}$ Input Cycle Time	1500		ns
$t_{w(ADL)}$	$\overline{\text{ADTRG}}$ Input LOW Pulse Width	200		ns

Table 5.41 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi Input Cycle Time	300		ns
$t_{w(CKH)}$	CLKi Input HIGH Pulse Width	150		ns
$t_{w(CKL)}$	CLKi Input LOW Pulse Width	150		ns
$t_{d(C-Q)}$	TXDi Output Delay Time		160	ns
$t_{h(C-Q)}$	TXDi Hold Time	0		ns
$t_{su(D-C)}$	RXDi Input Setup Time	100		ns
$t_{h(C-D)}$	RXDi Input Hold Time	90		ns

Table 5.42 External Interrupt $\overline{\text{INTi}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{\text{INTi}}$ Input HIGH Pulse Width	380		ns
$t_{w(INL)}$	$\overline{\text{INTi}}$ Input LOW Pulse Width	380		ns

$V_{CC1}=V_{CC2}=3V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.43 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.8**		30	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		0		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			30	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		0		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			25	ns
th(BCLK-ALE)	ALE Signal Output Hold Time		–4		ns
td(BCLK-RD)	RD Signal Output Delay Time			30	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			30	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

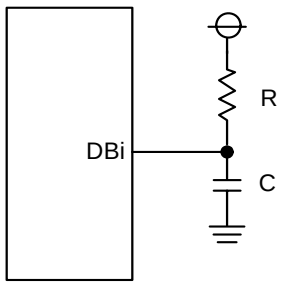
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 40[ns]$$ f(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL} / V_{CC1})$
   by a circuit of the right figure.
   For example, when V_{OL} = 0.2V_{CC1}, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC1} / V_{CC1})$
   = 6.7ns.



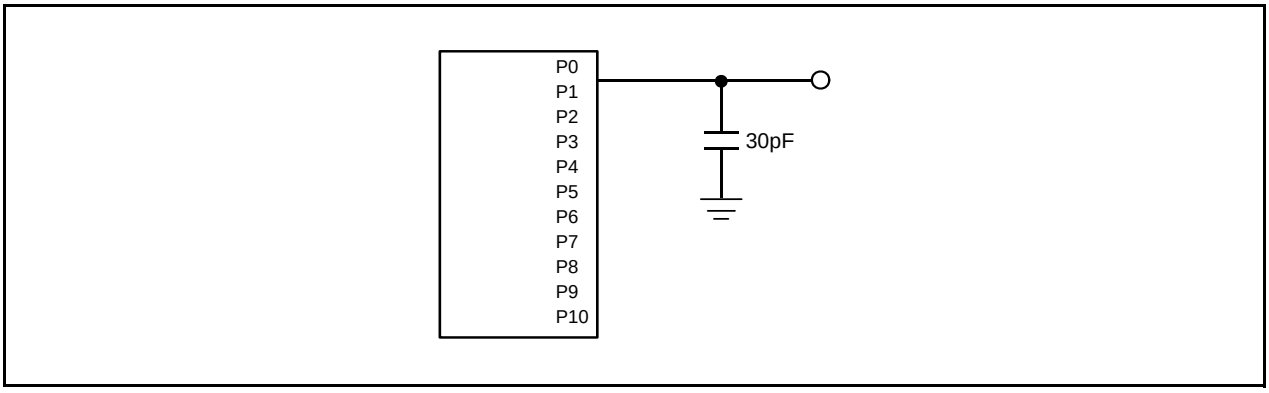


Figure 5.8 Ports P0 to P10 Measurement Circuit

Rev.	Date	Description	
		Page	Summary
		44	Figure 5.12 Timing Diagram (4) is added.
		45	Figure 5.13 Timing Diagram (5) is added.
1.10	Oct 01, 2005	2	Table 1.1 Performance Outline of M16C/30P Group is partly revised.
		4	Table 1.2 Product List is partly revised.
			Figure 1.2 Type No., Memory Size, and Package is partly revised.
		5	Table 1.3 Product Code of Mask ROM version Version for M16C/30P is added.
			Figure 1.3 Marking Diagram of Mask ROM Version for M16C/30P is added.
		6	Figure 1.4 Marking Diagram of ROM -less Version for M16C/30P is added.
		6	Table 1.4 Product Code of ROM-less version for M16C/30P is added.
		16	Figure 3.1 Memory Map is partly added.
		23	Table 5.2 information is revised.
1.11	May 31, 2006	4	1.4 Product List information is revised.
			Table 1.2 Product List is partly revised.
		5	Figure 1.2 Type No., Memory Size, and Package is partly added.
		7	Table 1.4 Product Code of Flash Memory version and ROM-less version for M16C/30P is partly revised.
			Figure 1.4 Marking Diagram of Flash Memory version and ROM-less Version for M16C/30P (Top View) is partly added.
		17	3. Memory information is revised.
			Figure 3.1 Memory Map is partly revised.
		18	Table 4.1 SFR Information(1) is partly revised.
		19	Table 4.2 SFR Information(2) is partly added.
		23	Table 5.1 Absolute Maximum Ratings information is revised.
		26	Table 5.4 Flash Memory Version Electrical Characteristics is added.
			Table 5.5 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics is added.
		28	Table 5.7 Electrical Characteristics(1) is partly deleted.
		29	Table 5.8 Electrical Characteristics (2) is partly revised.
		33	Table 5.23 Memory Expansion and Microprocessor Modes NOTES 3 is partly revised.
		34	Table 5.24 Memory Expansion and Microprocessor Modes NOTES 3 is partly revised.
		40	Table 5.25 Electrical Characteristics (1) is partly deleted.
		41	Table 5.26 Electrical Characteristics (2) is partly revised.
		45	Table 5.41 Memory Expansion and Microprocessor Modes NOTES 3 is partly revised.
		46	Table 5.42 Memory Expansion and Microprocessor Modes NOTES 3 is partly revised.

REVISION HISTORY	M16C/30P Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.20	Oct 17, 2006	1	Note is partly deleted.
		2	Table 1.1 Performance Outline of M16C/30P Group is partly added.
		4	Table 1.2 Product List is partly revised.
		5	Figure 1.2 Type No., Memory Size, and Package is added.
		7	Table 1.4 Product Code of One Time Flash version, Flash Memory version, and ROM-less version for M16C/30P is partly added.
		17	Figure 3.1 Memory Map is partly added.
		19	Table 4.2 SFR Information (2) is partly added.
		23	Table 5.1 Absolute Maximum Ratings is partly added.
		27	Table 5.6 One Time Flash Version Electrical Characteristics and Table 5.7 One Time Flash Version Program Voltage and Read Operation Voltage Characteristics is added.
		30	Table 5.10 Electrical Characteristics (2) is partly added.
		42	Table 5.28 Electrical Characteristics (2) is partly added.
1.21	Nov 02 2006	7	Table 1.4 Product Code of One Time Flash version, Flash Memory version, and ROM-less version for M16C/30P is partly revised.
1.22	Mar 30, 2007	4	Table 1.2 Product List (1) is partly revised.
		5	Table 1.3 Product List (2) is partly revised.
		19	Table 4.2 SFR Information (2) is partly revised.

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